


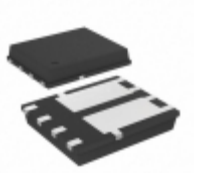

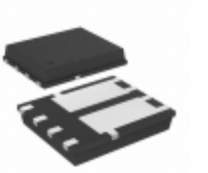

	<h2>SI7880ADP-T1-E3</h2>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI7880ADP-T1-E3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 40A PPAK SO-8</p> <p><b>Datenblätter:</b>  <a href="#">SI7880ADP-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 101189 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI7880ADP-T1-E3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET N-CH 30V 40A PPAK SO-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	101189 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	5.4W (Ta), 83W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	40A (Tc)
Rds On (Max) @ Id, Vgs	3 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	125nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	5600pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)

SI7880ADP-T1-E3 ist neu im Original, Suche SI7880ADP-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7880ADP-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7880ADP-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7880ADP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 40A PPAK SO-8</p>	 <p><b>SI7872DP-T1-GE3</b> Vishay / Siliconix MOSFET 2N-CH 30V 6.4A PPAK SO-8</p>	 <p><b>SI7872DP-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.4A PPAK SO-8</p>	 <p><b>SI7880DP</b> VISHAY VISHAY QFN</p>
 <p><b>SI7872DP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.4A PPAK SO-8</p>	 <p><b>SI7880ADP</b> SI SI7880ADP SI</p>	 <p><b>SI7872DP-T1-E3</b> Vishay / Siliconix MOSFET 2N-CH 30V 6.4A PPAK SO-8</p>	 <p><b>SI7880DP-T1</b> VISHAY SI7880DP-T1 VISHAY</p>

### heiße Teile

Mehr

 SI7864ADP-T1-GE3	 SI7864DP-T1-GE3	 SI7866ADP	 SI7866ADP-T1-E3	 SI7866ADP-T1-E3
 SI7866ADP-T1-GE3	 SI7866ADP-T1-GE3	 SI7866DP-T1	 SI7866DP-T1-E3	 SI7866DP-T1-GE3
 SI7868ADP	 SI7868ADP-T1-E3	 SI7868ADP-T1-E3	 SI7868ADP-T1-GE3	 SI7868ADP-T1-GE3
 SI7868DP-T1	 SI7868DP-T1-E3	 SI7868DP-T1-GE3	 SI786LG-T1	 SI786LG-T1-E3
 SI7872DP	 SI7872DP-T1-E3	 SI7872DP-T1-E3	 SI7872DP-T1-GE3	 SI7872DP-T1-GE3
 SI7880ADP-T1-E3	 SI7880ADP-T1-GE3	 SI7880ADP-T1-GE3	 SI7880DP-T1-GE3	 SI7882DP-T1-E3
 SI7882DP-T1-E3	 SI7882DP-T1-GE3	 SI7882DP-T1-GE3	 SI7884BDP	 SI7884BDP-T1-E3
 SI7884BDP-T1-E3	 SI7884BDP-T1-GE3	 SI7884BDP-T1-GE3	 SI7884DP-T1-E3	 SI7884DP-T1-GE3
 SI7886ADP-T1-E3	 SI7886ADP-T1-E3	 SI7886ADP-T1-GE3	 SI7886ADP-T1-GE3	 SI7886DP
 SI7886DP-T1	 SI7886DP-T1-E3	 SI7886DP-T1-GE3	 SI7888DP-T1-E3	 SI7888DP-T1-E3

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